

Features

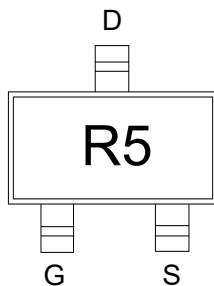
- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Application

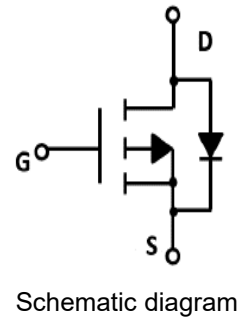
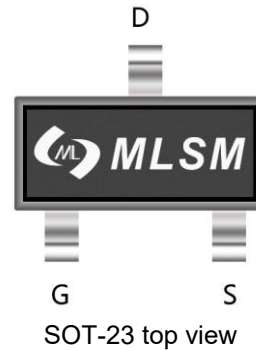
- Battery protection
- Load switch
- Power management

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-30V	102mΩ@-10V	-2.6A
	137mΩ@-4.5V	



R5: Device code



Halogen-Free

Marking and pin assignment

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage		-30	V
V _{GS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-2.6	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^{\circ}\text{C}$	-10	A
I_D	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	-2.6	A
P_D	Maximum Power Dissipation	$T_C=25^{\circ}\text{C}$	1.4	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		100	$^{\circ}\text{C/W}$

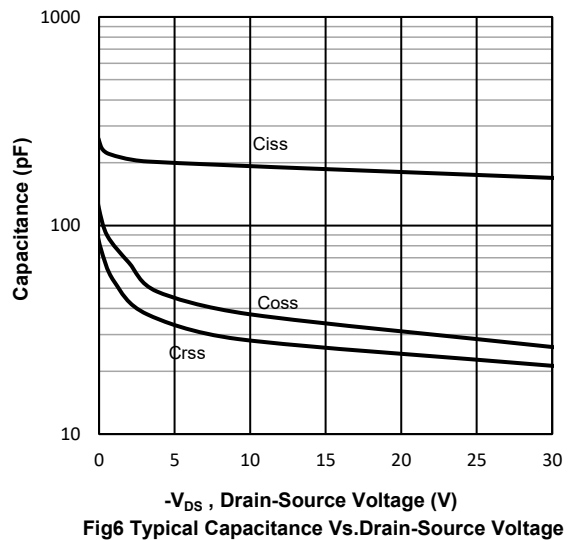
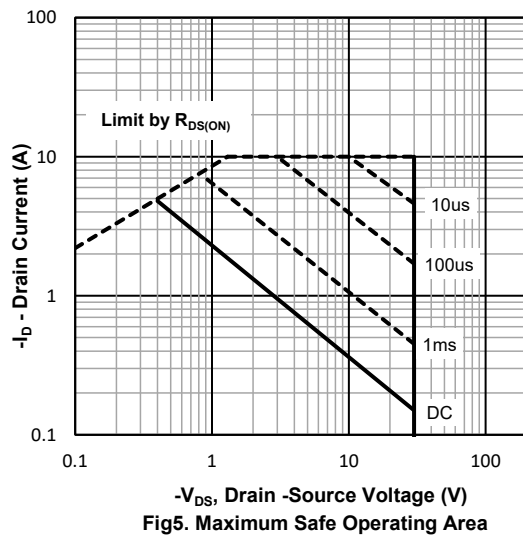
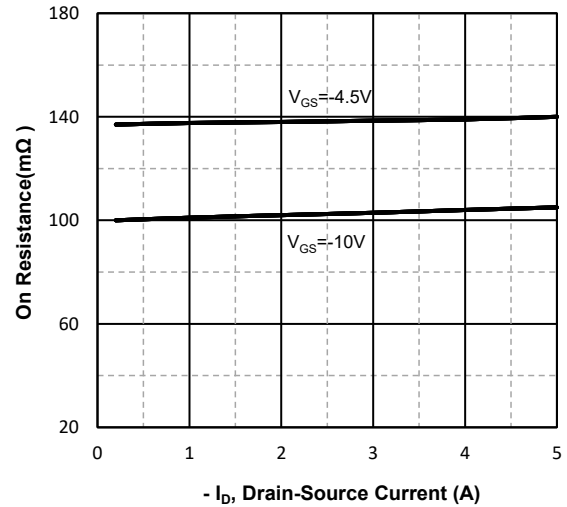
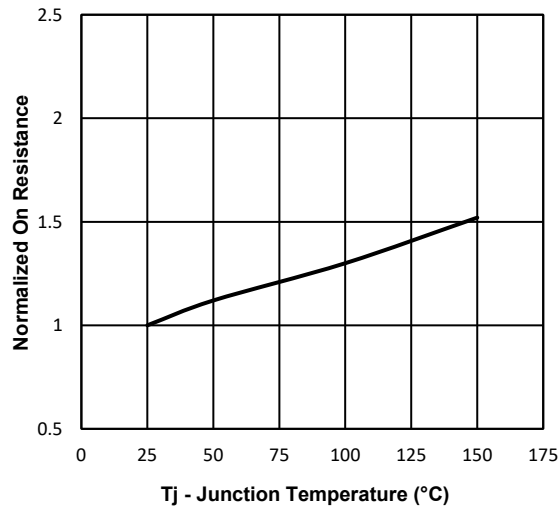
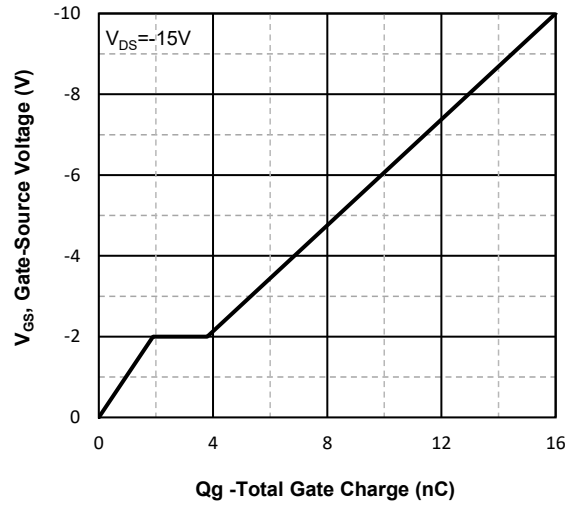
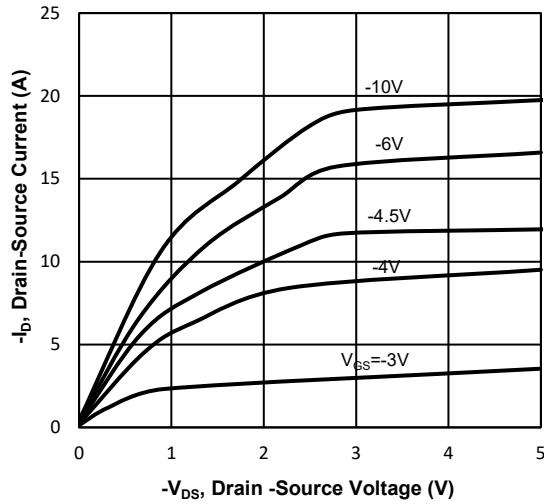
Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS3405	SOT-23	R5	3,000	45,000	180,000	7" reel

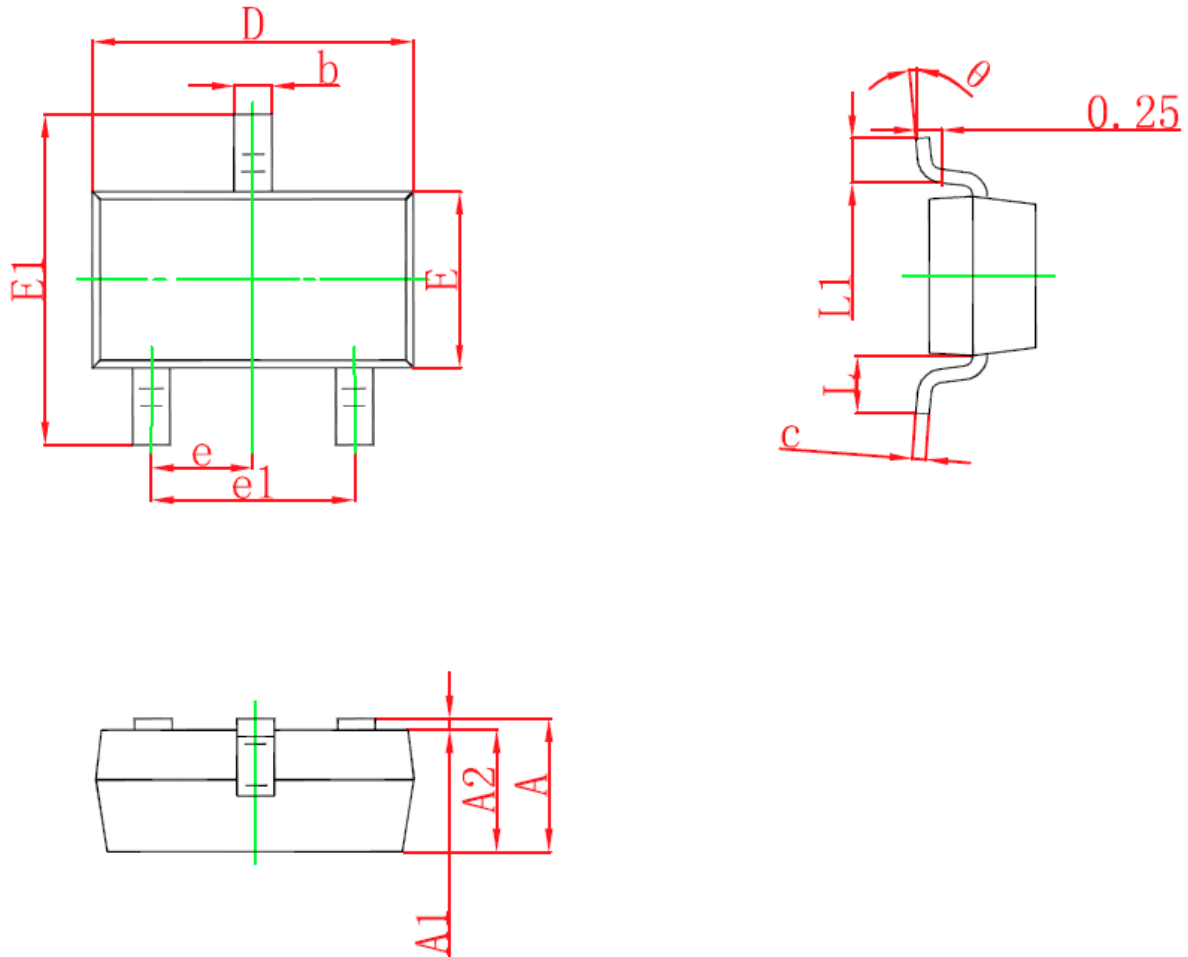
Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=-250μA	-30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-30V, VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=-250μA	-1.3	--	-2.3	V
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-2.6A	--	102	130	mΩ
		VGS=-4.5V, ID=-2.0A	--	137	180	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
CISS	Input Capacitance	VDS=-15V, VGS=0V, f=1MHz	--	190	--	pF
COSS	Output Capacitance		--	34	--	pF
CRSS	Reverse Transfer Capacitance		--	26	--	pF
Qg	Total Gate Charge	VDS=-15V, ID=-1A, VGS=-10V	--	6.1	--	nC
Qgs	Gate Source Charge		--	1.3	--	nC
Qgd	Gate Drain Charge		--	1.2	--	nC
Switching Characteristics						
td(on)	Turn-on Delay Time	VDS=-15V, ID=-1A, VGS=-10V, RG=3Ω	--	4	--	nS
tr	Turn-on Rise Time		--	22	--	nS
td(off)	Turn-Off Delay Time		--	20	--	nS
tf	Turn-Off Fall Time		--	27	--	nS
Source- Drain Diode Characteristics						
VSD	Forward on voltage	TJ=25°C, IS=-2.6A	--	--	-1.2	V

Typical Operating Characteristics



SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E1	2.250	2.550	0.088	0.100
E	1.200	1.400	0.047	0.055
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°